Sent By: Crawford PLLC;

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Feb-3-5:47PM;

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Page 2(NE)
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**PATENT** 

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Skala et al.

Examiner:

Im, J. M.

Serial No.:

09/874,606

Group Art Unit:

2811

Filed:

June 5, 2001

Docket No.:

PHA 51243A

Title:

PAD METALIZATION OVER ACTIVE CIRCUITRY

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence and the papers, as described hereinabove, are being transmitted via facsimile only-Formal Entry, to the attention of Examiner Im Assistant Commissioner for Patents, Washington, D.C. 20231, on February 3, 2003.

Facsmile No. (703) 872-9319

By: \\elly & Waltigney

## OFFICE ACTION AMENDMENT AND RESPONSE AFTER FINAL

**BOX AF** 

Assistant Commissioner for Patents Washington, D.C. 20231

**FAX RECEIVED** 

FEB 0 3 2003

Sir:

**TECHNOLOGY CENTER 2800** 

In response to the Final Office Action dated December 4, 2002, please reconsider the above-referenced application for patent in view of the following amendments and remarks.

## In the Claims:

Please replace the indicated claims as follows; a marked-up version of the claim amendments is attached hereto.

amer extended 15. 11

15. (Amended) A semiconductor chip having circuitry, the semiconductor chip comprising:

a metal bond pad over a portion of the circuitry;

a diffusion barrier layer over the metal bond pad; and

a metal layer over the diffusion barrier layer, the metal layer being configured and arranged for connecting to a wire bond, and the metal bond pad, the diffusion barrier layer and the metal layer all being insulated on at least two sides by passivation material.

wherein the diffusion layer is constructed and arranged to mitigate inter-metallic compounds forming as a reaction to the metal layer connecting to the wire bond, and the